

Toru Ujihara

List of Publications by Year in descending order

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214
papers

3,617
citations

147801

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docs citations

215
times ranked

1895
citing authors

#	ARTICLE	IF	CITATIONS
1	Solvent design aiming at solution property induced surface stability: A case study using SiC solution growth. <i>Journal of Crystal Growth</i> , 2022, 578, 126425.	1.5	7
2	Numerical investigation of solute evaporation in crystal growth from solution: A case study of SiC growth by TSSG method. <i>Journal of Crystal Growth</i> , 2022, 579, 126448.	1.5	6
3	Data-Driven Optimization and Experimental Validation for the Lab-Scale Mono-Like Silicon Ingot Growth by Directional Solidification. <i>ACS Omega</i> , 2022, 7, 6665-6673.	3.5	10
4	Nucleation sites of expanded stacking faults detected by <i>in operando</i> x-ray topography analysis to design epitaxial layers for bipolar-degradation-free SiC MOSFETs. <i>AIP Advances</i> , 2022, 12, .	1.3	5
5	Optimization of Flow Distribution by Topological Description and Machine Learning in Solution Growth of SiC. <i>Advanced Theory and Simulations</i> , 2022, 5, .	2.8	3
6	Explainable machine learning for the analysis of transport phenomena in top-seeded solution growth of SiC single crystal. <i>Journal of Thermal Science and Technology</i> , 2021, 16, JTST0009-JTST0009.	1.1	7
7	Geometrical design of a crystal growth system guided by a machine learning algorithm. <i>CrystEngComm</i> , 2021, 23, 2695-2702.	2.6	20
8	Chiral Optical Force Generated by a Superchiral Near-Field of a Plasmonic Triangle Trimer as Origin of Giant Bias in Chiral Nucleation: A Simulation Study. <i>Journal of Physical Chemistry C</i> , 2021, 125, 6209-6221.	3.1	10
9	Intensity Interference in a Coherent Spin-Polarized Electron Beam. <i>Physical Review Letters</i> , 2021, 126, 125501.	7.8	19
10	Synchrotron X-ray topographic image contrast variation of screw-type basal plane dislocations located at different depths below the crystal surface in 4H-SiC. <i>Acta Materialia</i> , 2021, 208, 116746.	7.9	10
11	Ordered Arrangement of Planar Faults with Picoscale Perfection in Titanium Oxide Natural Superlattices. <i>Journal of Physical Chemistry C</i> , 2021, 125, 11175-11181.	3.1	6
12	Two-Step Nanoparticle Crystallization via DNA-Guided Self-Assembly and the Nonequilibrium Dehydration Process. <i>Crystal Growth and Design</i> , 2021, 21, 4506-4515.	3.0	3
13	Control of microstructure and mechanical properties of sintered aluminum nitride through addition of aluminum nitride whiskers. <i>Journal of Asian Ceramic Societies</i> , 2021, 9, 1248-1254.	2.3	5
14	Adaptive process control for crystal growth using machine learning for high-speed prediction: application to SiC solution growth. <i>CrystEngComm</i> , 2021, 23, 1982-1990.	2.6	22
15	<i>In-operando</i> x-ray topography analysis of SiC metal-oxide-semiconductor field-effect transistors to visualize stacking fault expansion motions dynamically during operations. <i>Journal of Applied Physics</i> , 2021, 130, .	2.5	9
16	Immobilization of partial dislocations bounding double Shockley stacking faults in 4H-SiC observed by in situ synchrotron X-ray topography. <i>Materialia</i> , 2021, 20, 101246.	2.7	2
17	Kuwahara et al. Reply. <i>Physical Review Letters</i> , 2021, 127, 229602.	7.8	0
18	Bayesian optimization for a high- and uniform-crystal growth rate in the top-seeded solution growth process of silicon carbide under applied magnetic field and seed rotation. <i>Journal of Crystal Growth</i> , 2020, 532, 125437.	1.5	20

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19	Plasmonic Manipulation of Sodium Chlorate Chiral Crystallization: Directed Chirality Transfer via Contact-Induced Polymorphic Transformation and Formation of Liquid Precursor. <i>Crystal Growth and Design</i> , 2020, 20, 5493-5507.	3.0	7
20	Optimal Control of SiC Crystal Growth in the RF-TSSG System Using Reinforcement Learning. <i>Crystals</i> , 2020, 10, 791.	2.2	9
21	Temperature dependence of double Shockley stacking fault behavior in nitrogen-doped 4H-SiC studied by in-situ synchrotron X-ray topography. <i>Acta Materialia</i> , 2020, 194, 387-393.	7.9	6
22	Numerical Study of Three-Dimensional Melt Flows during the TSSG Process of SiC Crystal for the Influence of Input Parameters of RF-Coils and an External Rotating Magnetic Field. <i>Crystals</i> , 2020, 10, 111.	2.2	3
23	Effect of Crystal Orientation of Cu Current Collectors on Cycling Stability of Li Metal Anodes. <i>ACS Applied Materials & Interfaces</i> , 2020, 12, 9341-9346.	8.0	24
24	Design of High-quality SiC Solution Growth Condition Assisted by Machine Learning. <i>Materia Japan</i> , 2020, 59, 145-152.	0.1	0
25	Adjoint-based sensitivity analysis for the optimal crucible temperature profile in the RF-Heating TSSG-SiC crystal growth process. <i>Journal of Crystal Growth</i> , 2019, 517, 59-63.	1.5	6
26	In Situ Microscopic Observation on Surface Kinetics in Optical Trapping-Induced Crystal Growth: Step Formation, Wetting Transition, and Nonclassical Growth. <i>Crystal Growth and Design</i> , 2019, 19, 4138-4150.	3.0	3
27	The Effect of Crucible Rotation and Crucible Size in Topâ€Seeded Solution Growth of Singleâ€Crystal Silicon Carbide. <i>Crystal Research and Technology</i> , 2019, 54, 1900014.	1.3	5
28	The Prediction Model of Crystal Growth Simulation Built by Machine Learning and Its Applications. <i>Vacuum and Surface Science</i> , 2019, 62, 136-140.	0.1	6
29	Application of C-face dislocation conversion to 2 inch SiC crystal growth on an off-axis seed crystal. <i>CrystEngComm</i> , 2019, 21, 7260-7265.	2.6	14
30	Semi in-situ measurement of zincate ion concentration near zinc anode using background-oriented Schlieren technique. <i>Physical Review Research</i> , 2019, 1, .	3.6	0
31	High-speed prediction of computational fluid dynamics simulation in crystal growth. <i>CrystEngComm</i> , 2018, 20, 6546-6550.	2.6	48
32	In Situ Observation of Chiral Symmetry Breaking in NaClO ₃ Chiral Crystallization Realized by Thermoplasmonic Micro-Stirring. <i>Crystal Growth and Design</i> , 2018, 18, 4230-4239.	3.0	10
33	Development of angle-resolved spectroscopy system of electrons emitted from a surface with negative electron affinity state. <i>Review of Scientific Instruments</i> , 2018, 89, 073103.	1.3	10
34	Direct observation of stacking fault shrinkage in 4H-SiC at high temperatures by <i>in-situ</i> X-ray topography using monochromatic synchrotron radiation. <i>Applied Physics Letters</i> , 2018, 113, .	3.3	9
35	Numerical investigation of the effect of static magnetic field on the TSSG growth of SiC. <i>Journal of Crystal Growth</i> , 2018, 498, 140-147.	1.5	14
36	Crystal Orientation Dependence of Precipitate Structure of Electrodeposited Li Metal on Cu Current Collectors. <i>Crystal Growth and Design</i> , 2017, 17, 2379-2385.	3.0	21

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37	Global simulation of the induction heating TSSG process of SiC for the effects of Marangoni convection, free surface deformation and seed rotation. Journal of Crystal Growth, 2017, 470, 75-88.	1.5	29
38	Morphology of AlN whiskers grown by reacting N ₂ gas and Al vapor. Journal of Crystal Growth, 2017, 468, 576-580.	1.5	13
39	Numerical investigation of the transport phenomena occurring in the growth of SiC by the induction heating TSSG method. Journal of Crystal Growth, 2017, 474, 50-54.	1.5	16
40	Two-step SiC solution growth for dislocation reduction. Journal of Crystal Growth, 2017, 468, 874-878.	1.5	19
41	Plasmonic Heating-Assisted Laser-Induced Crystallization from a NaClO ₃ Unsaturated Mother Solution. Crystal Growth and Design, 2017, 17, 809-818.	3.0	15
42	Modification of the surface morphology of 4H-SiC by addition of Sn and Al in solution growth with SiCr solvents. Journal of Crystal Growth, 2017, 458, 37-43.	1.5	21
43	Phase transition process in DDAB supported lipid bilayer. Journal of Crystal Growth, 2017, 468, 88-92.	1.5	1
44	Temperature dependence of carrier relaxation time in gallium phosphide evaluated by photoemission measurements. AIP Advances, 2017, 7, 115314.	1.3	5
45	The Boersch effect in a picosecond pulsed electron beam emitted from a semiconductor photocathode. Applied Physics Letters, 2016, 109, .	3.3	32
46	Analysis of the carbon transport near the growth interface with respect to the rotational speed of the seed crystal during top-seeded solution growth of SiC. Japanese Journal of Applied Physics, 2016, 55, 125601.	1.5	17
47	Enantioselective amplification on circularly polarized laser-induced chiral nucleation from a NaClO ₃ solution containing Ag nanoparticles. CrystEngComm, 2016, 18, 7441-7448.	2.6	27
48	Characterization of V-Shaped Defects Formed during the 4H-SiC Solution Growth by Transmission Electron Microscopy and X-ray Topography Analysis. Crystal Growth and Design, 2016, 16, 5136-5140.	3.0	6
49	Spatial Distribution of Carrier Concentration in 4H-SiC; Crystal Grown by Solution Method. Materials Science Forum, 2016, 858, 57-60.	0.3	1
50	Polytype control by activity ratio of silicon to carbon during SiC solution growth using multicomponent solvents. Japanese Journal of Applied Physics, 2016, 55, 01AC01.	1.5	4
51	Conversion Behavior of Threading Screw Dislocations on C Face with Different Surface Morphology During 4H-SiC Solution Growth. Crystal Growth and Design, 2016, 16, 6436-6439.	3.0	21
52	Septin Interferes with the Temperature-Dependent Domain Formation and Disappearance of Lipid Bilayer Membranes. Langmuir, 2016, 32, 12823-12832.	3.5	13
53	Effect of magnesium ion concentration on two-dimensional structure of DNA-functionalized nanoparticles on supported lipid bilayer. Japanese Journal of Applied Physics, 2016, 55, 03DF11.	1.5	8
54	Thin film growth of CaFe ₂ As ₂ by molecular beam epitaxy. Superconductor Science and Technology, 2016, 29, 015013.	3.5	7

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55	Measurement of energy distribution of conduction electrons in superlattice by visible-light photoemission spectroscopy. , 2015, , .		0
56	B11-O-14Coherences of spin-polarized and pulsed electron beam extracted from a semiconductor photocathode in TEM. Microscopy (Oxford, England), 2015, 64, i17.1-i17.	1.5	0
57	Effect of aluminum addition on the surface step morphology of 4H-SiC grown from Si-Cr-C solution. Journal of Crystal Growth, 2015, 423, 45-49.	1.5	45
58	Non-uniform electrodeposition of zinc on the (0001) plane. Thin Solid Films, 2015, 590, 207-213.	1.8	26
59	Control of Interface Shape by Non-Axisymmetric Solution Convection in Top-Seeded Solution Growth of SiC Crystal. Materials Science Forum, 2015, 821-823, 18-21.	0.3	3
60	3C-SiC Crystal on Sapphire by Solution Growth Method. Materials Science Forum, 2015, 821-823, 185-188.	0.3	0
61	Coherence of a spin-polarized electron beam emitted from a semiconductor photocathode in a transmission electron microscope. Applied Physics Letters, 2014, 105, .	3.3	38
62	Growth of a smooth CaF ₂ layer on NdFeAsO thin film. Journal of Physics: Conference Series, 2014, 507, 012047.	0.4	3
63	Direct measurement of conduction miniband structure in superlattice by visible-light photoemission spectroscopy. , 2014, , .		1
64	Increase in the Growth Rate by Rotating the Seed Crystal at High Speed during the Solution Growth of SiC. Materials Science Forum, 2014, 778-780, 63-66.	0.3	10
65	Growth rate and surface morphology of 4H-SiC crystals grown from Si-Cr-C and Si-Cr-Al-C solutions under various temperature gradient conditions. Journal of Crystal Growth, 2014, 401, 681-685.	1.5	58
66	The strain effect on the superconducting properties of BaFe ₂ (As, P) ₂ thin films grown by molecular beam epitaxy. Superconductor Science and Technology, 2014, 27, 065005.	3.5	26
67	Low-dislocation-density 4H-SiC crystal growth utilizing dislocation conversion during solution method. Applied Physics Express, 2014, 7, 065501.	2.4	51
68	Emergence and Amplification of Chirality via Achiral-Chiral Polymorphic Transformation in Sodium Chlorate Solution Growth. Crystal Growth and Design, 2014, 14, 3596-3602.	3.0	19
69	Top-seeded solution growth of three-inch-diameter 4H-SiC using convection control technique. Journal of Crystal Growth, 2014, 395, 68-73.	1.5	59
70	Different behavior of threading edge dislocation conversion during the solution growth of 4H-SiC depending on the Burgers vector. Acta Materialia, 2014, 81, 284-290.	7.9	34
71	Solubility measurement of a metastable achiral crystal of sodium chlorate in solution growth. Journal of Crystal Growth, 2014, 394, 106-111.	1.5	15
72	Forming two-dimensional structure of DNA-functionalized Au nanoparticles via lipid diffusion in supported lipid bilayers. Journal of Crystal Growth, 2014, 401, 494-498.	1.5	11

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73	Nitrogen doping of 4H-SiC by the top-seeded solution growth technique using Si-Ti solvent. Journal of Crystal Growth, 2014, 392, 60-65.	1.5	32
74	Influence of Solution Flow on Step Bunching in Solution Growth of SiC Crystals. Crystal Growth and Design, 2013, 13, 3691-3696.	3.0	35
75	Achiral Metastable Crystals of Sodium Chlorate Forming Prior to Chiral Crystals in Solution Growth. Crystal Growth and Design, 2013, 13, 5188-5192.	3.0	26
76	Electron spectroscopy of conduction electrons excited by visible light utilizing NEA surface. , 2013, , .		2
77	Critical current density and grain boundary property of BaFe ₂ (As,P) ₂ thin films. Physica C: Superconductivity and Its Applications, 2013, 494, 181-184.	1.2	38
78	Phase-locking of oscillating images using laser-induced spin-polarized pulse TEM. Microscopy (Oxford,) Tj ETQq0 0 0 0 BT /Overlock 10 T	1.5	6
79	Evolution of threading screw dislocation conversion during solution growth of 4H-SiC. APL Materials, 2013, 1, .	5.1	50
80	Ultra-high-resolution direct observation of mini-bands formed in InGaAs/AlGaAs superlattice. , 2013, , .		1
81	Direct Growth of AlN Single Crystal on Sapphire by Solution Growth Method. Japanese Journal of Applied Physics, 2013, 52, 08JE17.	1.5	10
82	30-kV spin-polarized transmission electron microscope with GaAs-GaAsP strained superlattice photocathode. Applied Physics Letters, 2012, 101, .	3.3	52
83	High-Efficiency Conversion of Threading Screw Dislocations in 4H-SiC by Solution Growth. Applied Physics Express, 2012, 5, 115501.	2.4	67
84	Development of Spin-Polarized Pulsed TEM. Journal of Physics: Conference Series, 2012, 371, 012004.	0.4	4
85	Polytype Transformation by Replication of Stacking Faults Formed by Two-Dimensional Nucleation on Spiral Steps during SiC Solution Growth. Crystal Growth and Design, 2012, 12, 3209-3214.	3.0	30
86	Polytype-selective growth of SiC by supersaturation control in solution growth. Journal of Crystal Growth, 2012, 360, 176-180.	1.5	20
87	Analysis of thickness modulation in GaAs/GaAsP strained superlattice by TEM observation. Journal of Crystal Growth, 2012, 353, 84-87.	1.5	3
88	Substrate dependence of the superconducting properties of NdFeAs(O,F) thin films. Solid State Communications, 2012, 152, 735-739.	1.9	25
89	Anomalous Diffusion in Supported Lipid Bilayers Induced by Oxide Surface Nanostructures. Langmuir, 2011, 27, 9662-9665.	3.5	33
90	Formation process of 3C-SiC on 6H-SiC (0001) by low-temperature solution growth in Si-Sc-C system. Journal of Crystal Growth, 2011, 335, 94-99.	1.5	21

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91	Molecular Beam Epitaxy Growth of Superconducting NdFeAs(O,F) Thin Films Using a F-Getter and a Novel F-Doping Method. Applied Physics Express, 2011, 4, 083102.	2.4	32
92	Epitaxial growth of LaFeAs(O,F) thin films by molecular beam epitaxy. Physica C: Superconductivity and Its Applications, 2011, 471, 1174-1176.	1.2	6
93	Increase of spectral width of stacked InAs quantum dots on GaAs by controlling spacer layer thickness. Journal of Crystal Growth, 2011, 318, 1113-1116.	1.5	0
94	High-quality and large-area 3C-SiC growth on 6H-SiC(0 0 0 1) seed crystal with top-seeded solution method. Journal of Crystal Growth, 2011, 318, 389-393.	1.5	20
95	Defect Evaluation of SiC Crystal Grown by Solution Method: The Study by Synchrotron X-Ray Topography and Etching Method. Materials Science Forum, 2011, 679-680, 28-31.	0.3	6
96	Effects of defects and local thickness modulation on spin-polarization in photocathodes based on GaAs/GaAsP strained superlattices. Journal of Applied Physics, 2010, 108, 094509.	2.5	12
97	Real Time Magnetic Imaging by Spin-Polarized Low Energy Electron Microscopy with Highly Spin-Polarized and High Brightness Electron Gun. Applied Physics Express, 2010, 3, 026601.	2.4	41
98	In situ growth of superconducting NdFeAs(O,F) thin films by molecular beam epitaxy. Applied Physics Letters, 2010, 97, 042509.	3.3	57
99	8.5: Effects of defects and local thickness modulation on spin-polarization in photocathodes based on GaAs/GaAsP strained superlattices. , 2010, , .		0
100	Strain of GaAs/GaAsP Superlattices Used as Spin-Polarized Electron Photocathodes, Determined by X-Ray Diffraction. E-Journal of Surface Science and Nanotechnology, 2010, 8, 125-130.	0.4	1
101	Epitaxial Growth of NdFeAsO Thin Films by Molecular Beam Epitaxy. Applied Physics Express, 2009, 2, 093002.	2.4	52
102	Study of minority carrier diffusion length in multicrystalline silicon solar cells using photoassisted Kelvin probe force microscopy. Applied Physics Letters, 2009, 95, 191908.	3.3	19
103	Anisotropy of mosaic structure of GaAsP layers grown on GaAs substrates. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 1785-1789.	1.8	1
104	Polytype and Crystal Quality of SiC Crystals Grown on 3C-SiC by Seeded Solution Method. Materials Science Forum, 2009, 615-617, 27-30.	0.3	4
105	Effects of Applied Voltage on the Size of Phase-Separated Domains in DMPS-DOPC Lipid Binary Bilayers Supported on SiO ₂ /Si Substrates. Transactions of the Materials Research Society of Japan, 2009, 34, 217-220.	0.2	0
106	Local Condensation of Artificial Raft Domains under Light Irradiation in Supported Lipid Bilayer of PSM-DOPC-Cholesterol System. Transactions of the Materials Research Society of Japan, 2009, 34, 179-182.	0.2	0
107	Shape Transformation of Adsorbed Vesicles on Oxide Surfaces: Effect of Substrate Material and Photo-Irradiation. Transactions of the Materials Research Society of Japan, 2009, 34, 183-188.	0.2	3
108	High Brightness and high polarization electron source using transmission photocathode. , 2009, , .		0

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109	Effects of absorbed group-V atoms on the size distribution and optical properties of InAsP quantum dots fabricated by the droplet hetero-epitaxy. Journal of Crystal Growth, 2008, 310, 2239-2243.	1.5	6
110	Solution growth of high-quality 3C-SiC crystals. Journal of Crystal Growth, 2008, 310, 1438-1442.	1.5	32
111	Highly spin-polarized electron photocathode based on GaAs/GaAsP superlattice grown on mosaic-structured buffer layer. Journal of Crystal Growth, 2008, 310, 5039-5043.	1.5	24
112	Lipid Bilayer Membrane with Atomic Step Structure: Supported Bilayer on a Step-and-Terrace TiO ₂ (100) Surface. Langmuir, 2008, 24, 11567-11576.	3.5	76
113	Local Concentration of Gel Phase Domains in Supported Lipid Bilayers under Light Irradiation in Binary Mixture of Phospholipids Doped with Dyes for Photoinduced Activation. Langmuir, 2008, 24, 10974-10980.	3.5	11
114	Stability Growth Condition for 3C-SiC Crystals by Solution Technique. Materials Science Forum, 2008, 600-603, 63-66.	0.3	4
115	High brightness and high polarization electron source using transmission photocathode with GaAs-GaAsP superlattice layers. Journal of Applied Physics, 2008, 103, .	2.5	49
116	Minority carrier lifetime in polycrystalline silicon solar cells studied by photoassisted Kelvin probe force microscopy. Applied Physics Letters, 2008, 93, .	3.3	64
117	Minority carrier dynamics in polycrystalline silicon solar cells studied by photo-assisted Kelvin probe force microscopy. Conference Record of the IEEE Photovoltaic Specialists Conference, 2008, , .	0.0	0
118	2P-229 In situ Observation of Molecular Diffusion in Supported Lipid Bilayer on Oxide Surfaces by Substrate-Derestricted Single-Molecule Tracking(The 46th Annual Meeting of the Biophysical Society) Tj ETQq0 0 0 rgBT /Overlock 10 T650 57 Td		
119	Photovoltage Mapping on Polycrystalline Silicon Solar Cells by Kelvin Probe Force Microscopy with Piezoresistive Cantilever. Japanese Journal of Applied Physics, 2007, 46, 5548.	1.5	37
120	Thermal emittance measurements for electron beams produced from bulk and superlattice negative electron affinity photocathodes. Journal of Applied Physics, 2007, 102, 024904.	2.5	33
121	Development of the New Type Polarized Electron Source for SPLEEM. AIP Conference Proceedings, 2007, , .	0.4	1
122	Supported lipid bilayer membranes on SiO ₂ and TiO ₂ : substrate effects on membrane formation and shape transformation. , 2007, , .		8
123	Desorption Time of As Adsorbed on GaInAs Surface Analyzed by X-ray CTR Scattering. Indium Phosphide and Related Materials Conference (IPRM), IEEE International Conference on, 2007, , .	0.0	1
124	Effect of Li doping on photoluminescence from Er, O-codoped GaAs. Journal of Crystal Growth, 2007, 298, 69-72.	1.5	12
125	Growth of SiC Single Crystal from Si-C-(Co, Fe) Ternary Solution. Materials Science Forum, 2006, 527-529, 115-118.	0.3	5
126	2P293 Formation of domains in fluorescent lipids doped DMPC-DOPC binary bilayers supported on SiO ₂ /Si substrates under local light irradiation.(40. Membrane structure,Poster) Tj ETQq0 0 0 rgBT /Overlock 10 T650 57 Td(Session,A		

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127	Pattern size effect on source supply process for sub-micrometer scale selective area growth by organometallic vapor phase epitaxy. <i>Journal of Crystal Growth</i> , 2006, 289, 89-95.	1.5	15
128	Photovoltage Mapping on Polycrystalline Silicon Solar Cells through Potential Measurements by Atomic Force Microscopy with Piezoresistive Cantilever. <i>Japanese Journal of Applied Physics</i> , 2006, 45, 2128-2131.	1.5	16
129	Solution Growth of SiC Crystal with High Growth Rate Using Accelerated Crucible Rotation Technique. <i>Materials Science Forum</i> , 2006, 527-529, 119-122.	0.3	38
130	Size uniformity of InAs dots on mesa-structure templates on (001) InP substrates grown by droplet metal-organic vapor phase epitaxy method. <i>Applied Physics Letters</i> , 2006, 89, 083110.	3.3	10
131	Growth of InGaAs and SiGe homogeneous bulk crystals which have complete miscibility in the phase diagrams. <i>International Journal of Materials and Product Technology</i> , 2005, 22, 185.	0.2	5
132	Effects of vicinal steps on the island growth and orientation of epitaxially grown perylene-3,4,9,10-tetracarboxylic dianhydride (PTCDA) thin film crystals on a hydrogen-terminated Si(111) substrate. <i>Journal of Crystal Growth</i> , 2005, 273, 594-602.	1.5	9
133	Growth of SiGe-on-insulator and its application as a substrate for epitaxy of strained-Si layer. <i>Journal of Crystal Growth</i> , 2005, 275, e1203-e1207.	1.5	3
134	A simple approach to determine preferential growth orientation using multiple seed crystals with random orientations and its utilization for seed optimization to restrain polycrystallization of SiGe bulk crystal. <i>Journal of Crystal Growth</i> , 2005, 276, 393-400.	1.5	16
135	Structural properties of directionally grown polycrystalline SiGe for solar cells. <i>Journal of Crystal Growth</i> , 2005, 275, 467-473.	1.5	14
136	Crystal quality of a 6H-SiC layer grown over macrodefects by liquid-phase epitaxy: a Raman spectroscopic study. <i>Thin Solid Films</i> , 2005, 476, 206-209.	1.8	27
137	Influence of growth temperature on minority-carrier lifetime of Si layer grown by liquid phase epitaxy using Ga solvent. <i>Journal of Applied Physics</i> , 2005, 98, 073708.	2.5	1
138	Crystalline Quality Evaluation of 6H-SiC Bulk Crystals Grown from Si-Ti-C Ternary Solution. <i>Materials Science Forum</i> , 2005, 483-485, 13-16.	0.3	21
139	Relationship between Device Performance and Grain Boundary Structural Configuration in a Solar Cell Based on Multicrystalline SiGe. <i>Japanese Journal of Applied Physics</i> , 2004, 43, L250-L252.	1.5	2
140	Ge composition dependence of properties of solar cells based on multicrystalline SiGe with microscopic compositional distribution. <i>Journal of Applied Physics</i> , 2004, 96, 1238-1241.	2.5	32
141	Effects of spacer thickness on quantum efficiency of the solar cells with embedded Ge islands in the intrinsic layer. <i>Applied Physics Letters</i> , 2004, 84, 2802-2804.	3.3	22
142	Crystal Quality Evaluation of 6H-SiC Layers Grown by Liquid Phase Epitaxy around Micropipes using Micro-Raman Scattering Spectroscopy. <i>Materials Science Forum</i> , 2004, 457-460, 633-636.	0.3	5
143	TEM Studies on the Initial Stage of Seeded Solution Growth of 6H-SiC using Metal Solvent. <i>Materials Science Forum</i> , 2004, 457-460, 347-350.	0.3	0
144	Successful Growth of In _x Ga _{1-x} As (x>0.18) Single Bulk Crystal Directly on GaAs Seed Crystal with Preferential Orientation. <i>Japanese Journal of Applied Physics</i> , 2004, 43, L907-L909.	1.5	1

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145	Fabrication of solar cell with stacked Ge islands for enhanced absorption in the infrared regime. Thin Solid Films, 2004, 451-452, 604-607.	1.8	7
146	Epitaxial relation and island growth of perylene-3,4,9,10-tetracarboxylic dianhydride (PTCDA) thin film crystals on a hydrogen-terminated Si(111) substrate. Journal of Crystal Growth, 2004, 262, 196-201.	1.5	20
147	Phase diagram of growth mode for the SiGe/Si heterostructure system with misfit dislocations. Journal of Crystal Growth, 2004, 260, 372-383.	1.5	13
148	In situ observation of elementary growth steps on the surface of protein crystals by laser confocal microscopy. Journal of Crystal Growth, 2004, 262, 536-542.	1.5	98
149	In-situ observations of melt growth behavior of polycrystalline silicon. Journal of Crystal Growth, 2004, 262, 124-129.	1.5	69
150	Effects of growth temperature on the surface morphology of silicon thin films on (111) silicon monocrystalline substrate by liquid phase epitaxy. Journal of Crystal Growth, 2004, 266, 467-474.	1.5	7
151	Grain growth behaviors of polycrystalline silicon during melt growth processes. Journal of Crystal Growth, 2004, 266, 441-448.	1.5	101
152	Fabrication of SiGe-on-insulator by rapid thermal annealing of Ge on Si-on-insulator substrate. Applied Surface Science, 2004, 224, 95-98.	6.1	10
153	On the origin of strain fluctuation in strained-Si grown on SiGe-on-insulator and SiGe virtual substrates. Applied Physics Letters, 2004, 85, 1335-1337.	3.3	21
154	Solution Growth of Self-Standing 6H-SiC Single Crystal Using Metal Solvent. Materials Science Forum, 2004, 457-460, 123-126.	0.3	30
155	Molten metal flux growth and properties of CrSi ₂ . Journal of Alloys and Compounds, 2004, 383, 319-321.	5.5	12
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